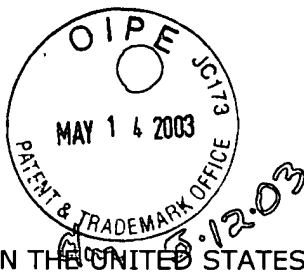


MTS-2700US1



PATENT

5.2003  
C. Moore

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applicant: Yuji Judai : Art Unit: 2814  
Serial No.: November 21, 2001 : Examiner: H. Weiss  
Filed: 09/990,474 :  
FOR: A METHOD FOR FORMING A :  
SEMICONDUCTOR DEVICE (AS AMENDED) :

**AMENDMENT**

Commissioner for Patents  
P.O. Box 1450  
Alexandria, VA 22313-1450

S I R :

Responsive to the Official Action dated **January 10, 2003**, please amend the  
above-identified application as follows:

**IN THE CLAIMS:**

Please cancel claims 8 and 9.

Please amend the claims to read as indicated:

C1  
5. (Twice Amended) The method for forming a semiconductor device  
according to claim 16, in which said step f1) comprises:  
depositing said second insulating film using a TEOS-CVD method utilizing TEOS  
activated by O<sub>3</sub>.

C2  
11. (Twice Amended) The method for forming a semiconductor device  
according to claim 16, wherein said upper layer is an Al layer.

12. (Twice Amended) The method for forming a semiconductor device  
according to claim 11, wherein

said step of depositing said Al layer comprises sputtering while heating said circuit  
board in a temperature range of 100 to 400°C.

C3  
16. (Amended) A method for forming a semiconductor device, comprising the  
steps of: